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NPN Silicon RF Transistor*

- For low noise, high-gain broadband amplifiers at collector currents from 1 mA to 20 mA
- $f_T = 9$ GHz, F = 1 dB at 1 GHz
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101
- * Short term description





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFR949L3	RK	1 = B	2 = E	3 = C	TSLP-3-1

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{\sf CEO}$	10	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I _C	50	mA
Base current	I_{B}	5	
Total power dissipation ²⁾	P _{tot}	250	mW
<i>T</i> _S ≤ 101 °C			
Junction temperature	T_{i}	150	°C
Ambient temperature	T_{A}	-65 150	
Storage temperature	$T_{ m stg}$	-65 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ³⁾	R_{thJS}	≤ 195	K/W

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¹Pb-containing package may be available upon special request

 $^{^2}T_{\mbox{\scriptsize S}}$ is measured on the collector lead at the soldering point to the pcb

 $^{^3}$ For calculation of R_{thJA} please refer to Application Note Thermal Resistance



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics				•	•
Collector-emitter breakdown voltage	V _{(BR)CEO}	10	-	-	V
$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$, ,				
Collector-emitter cutoff current	I _{CES}	-	-	100	μΑ
$V_{CE} = 20 \text{ V}, \ V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	/ _{EBO}	-	-	0.1	μΑ
$V_{\rm EB} = 1 \text{ V}, I_{\rm C} = 0$					
DC current gain-	h _{FE}	100	140	180	-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 6 V, pulse measured					



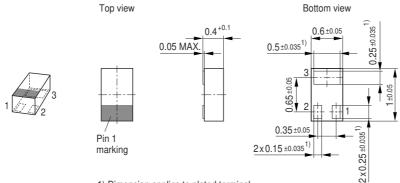
Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter Parameter Characteristics at $I_A = 25^{\circ}$ C, unless	Symbol		Values		
		min.	typ.	max.	
AC Characteristics (verified by random sampling	g)				
Transition frequency	f _T	7	9	-	GHz
$I_{\rm C} = 15 \text{ mA}, \ V_{\rm CE} = 6 \text{ V}, \ f = 1 \text{ GHz}$					
Collector-base capacitance	C_{cb}	-	0.25	0.4	рF
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0,$					
emitter grounded					
Collector emitter capacitance	C_{ce}	-	0.15	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C_{eb}	-	0.7	-	
$V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{CB} = 0$,					
collector grounded					
Noise figure	F				dB
$I_{\rm C} = 5 \text{ mA}, \ V_{\rm CE} = 6 \text{ V}, \ Z_{\rm S} = Z_{\rm Sopt},$					
f = 1 GHz		-	1	2.5	
$I_{C} = 3 \text{ mA}, \ V_{CE} = 8 \text{ V}, \ Z_{S} = Z_{Sopt} \ ,$					
f = 1.8 GHz		-	1.3	-	
Power gain ¹⁾	G _{ms}	-	21.5	-	-
$I_{\rm C} = 10 \text{ mA}, \ V_{\rm CE} = 8 \text{ V}, \ Z_{\rm S} = Z_{\rm Sopt} \ ,$					
$Z_{L} = Z_{Lopt}$, $f = 900 \text{ MHz}$					
Power gain, maximum available ¹⁾	G _{ma}	-	15.5	-	dB
$I_{\rm C} = 10 \text{ mA}, \ V_{\rm CE} = 8 \text{ V}, \ Z_{\rm S} = Z_{\rm Sopt} \ ,$					
$Z_{L} = Z_{Lopt}$, $f = 1.8 \text{ GHz}$					
Transducer gain	$ S_{21e} ^2$				dB
$I_{\rm C} = 15 \text{ mA}, \ V_{\rm CE} = 6 \text{ V}, \ Z_{\rm S} = Z_{\rm L} = 50 \Omega$					
f = 1 GHz		14	17	-	
$I_{\rm C} = 10 \text{ mA}, \ V_{\rm CE} = 8 \text{ V}, \ Z_{\rm S} = Z_{\rm L} = 50 \Omega \ ,$					
f = 1.8 GHz		-	12	-	

 $^{^{1}}G_{\text{ma}} = |S_{21} / S_{12}| \text{ (k-(k^2-1)^{1/2})}, G_{\text{ms}} = |S_{21} / S_{12}|$



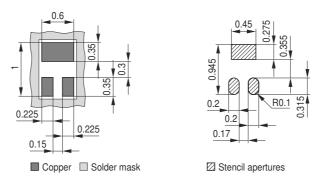
Package Outline



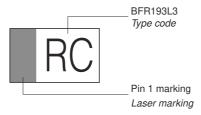
1) Dimension applies to plated terminal

Foot Print

For board assembly information please refer to Infineon website "Packages"

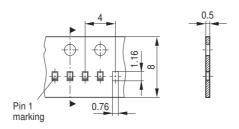


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel



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